ABSTRACT

A method is provided for forming one or more doped layers using ion-implantation in the fabrication of thyristor devices. For example, these thyristors may be made from single crystalline silicon carbide. According to one aspect of the invention, one of the required layers is formed by introducing dopants after crystal growth as opposed to conventional methods which involve doping during crystal growth. Specifically, impurities may be introduced by using the technique of ion implantation.